

**Silicon PNP Power Transistors**

**2SA957 2SA958**

**DESCRIPTION**

- With TO-220 package
- High breakdown voltage
- High power dissipation

**APPLICATIONS**

- For general purpose applications

**PINNING**

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

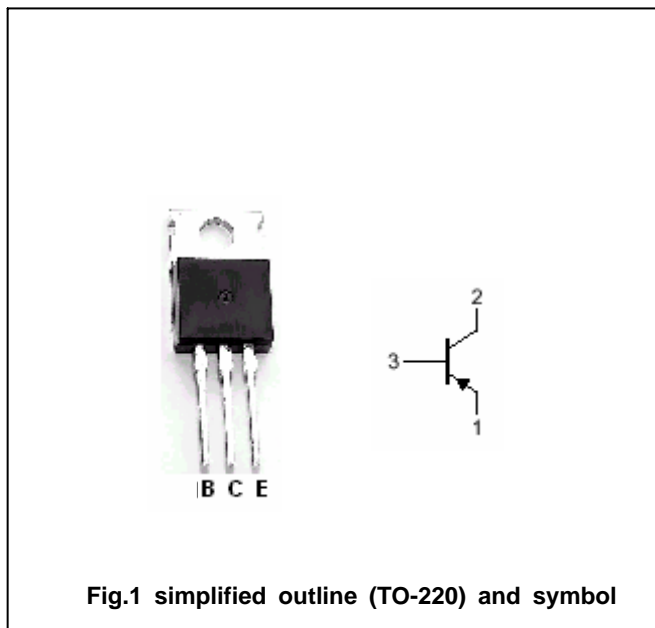


Fig.1 simplified outline (TO-220) and symbol

**Absolute maximum ratings(Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	2SA957	-150	V
		2SA958	-200	
V <sub>CEO</sub>	Collector-emitter voltage	2SA957	-150	V
		2SA958	-200	
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-6	V
I <sub>C</sub>	Collector current		-2.0	A
I <sub>B</sub>	Base current		-1.0	A
P <sub>T</sub>	Total power dissipation	T <sub>C</sub> =25	30	W
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(BR)</sub>	Collector-emitter breakdown voltage	2SA957	I <sub>C</sub> =-25mA, I <sub>B</sub> =0			V
		2SA958				
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-0.7A; I <sub>B</sub> =-0.07A			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	2SA957				μA
		2SA958				
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-6V; I <sub>C</sub> =0			-1.0	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-0.7A; V <sub>CE</sub> =-10V	40			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.2A; V <sub>CE</sub> =-12V		20		MHz

## Switching times resistive load

t <sub>r</sub>	Rise time	I <sub>C</sub> =-1.0A I <sub>B1</sub> =- I <sub>B2</sub> =-0.1A R <sub>L</sub> =20 Ω; V <sub>CC</sub> =-20V		0.4		μs
t <sub>s</sub>	Storage time			1.5		μs
t <sub>f</sub>	Fall time			0.5		μs

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PACKAGE OUTLINE

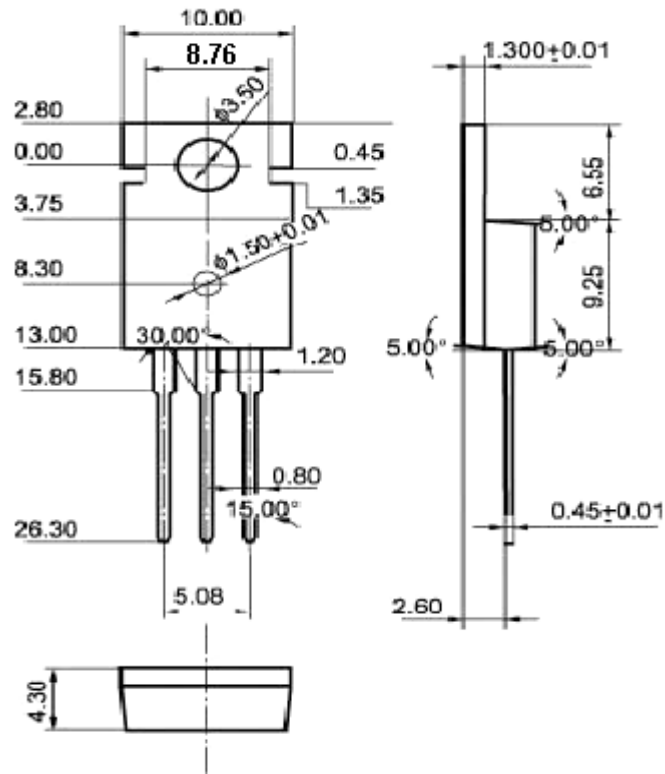


Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)